

N-channel TrenchMOS logic level FET 19 March 2014

Product data sheet

### 1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

### 3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

### 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	-	55	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>sp</sub> = 25 °C; <u>Fig. 2; Fig. 3</u>	-	-	5.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; <u>Fig. 1</u>	-	-	8	W
Static char	acteristics	I I	1			
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-	-	161	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-	116	137	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 12;</u> <u>Fig. 13</u>	-	128	150	mΩ
Dynamic cl	haracteristics	· · · · · · · · · · · · · · · · · · ·	I			
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; V <sub>DS</sub> = 44 V; T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	2.8	-	nC
Avalanche	ruggedness	· · · · · · · · · · · · · · · · · · ·	1			
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 5.5 A; $V_{sup} \le 55$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	22	mJ

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	4	D
2	D	drain		
3	S	source		G
4	D	drain	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	mbb076 S

### 6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BUK98150-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			
BUK98150-55A/CU	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK98150-55A	915055A
BUK98150-55A/CU	915055

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	55	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ	-	55	V
V <sub>GS</sub>	gate-source voltage		-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; <u>Fig. 1</u>	-	8	W
I <sub>D</sub>	drain current	T <sub>sp</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2; Fig. 3</u>	-	5.5	А
		T <sub>sp</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>	-	3	А
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; pulsed; $t_p \le 10 \ \mu s; \frac{Fig. 3}{2}$	-	22	А

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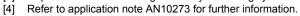
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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	150	°C
Tj	junction temperature			-55	150	°C
Source-drain	diode					
I <sub>S</sub>	source current	T <sub>sp</sub> = 25 °C		-	5.5	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{sp} = 25 \ ^{\circ}C$		-	22	А
Avalanche ru	lggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_D = 5.5 \text{ A}; \ V_{sup} \leq 55 \text{ V}; \ R_{GS} = 50 \Omega; \\ V_{GS} = 5 \text{ V}; \ T_{j(init)} = 25 \text{ °C}; \ unclamped \end{split}$		-	22	mJ
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy	Fig. 4	[1][2][3]	4 <del>]</del>	-	J

[1]

- Value not quoted. Repetitive rating defined in avalanche rating figure. Single-pulse avalanche rating limited by maximum junction temperature of 150 °C. [2]
- [3] Repetitive avalanche rating limited by an average junction temperature of 145 °C.



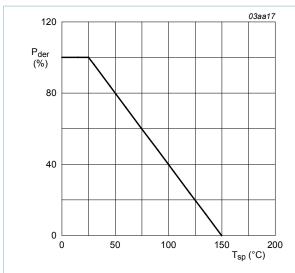


Fig. 1. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

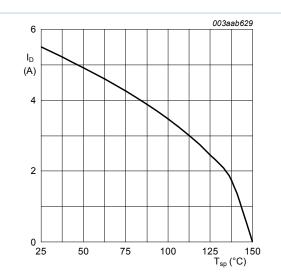


Fig. 2. Continuous drain current as a function of solder point temperature

 $V_{GS} \ge 5V$ 

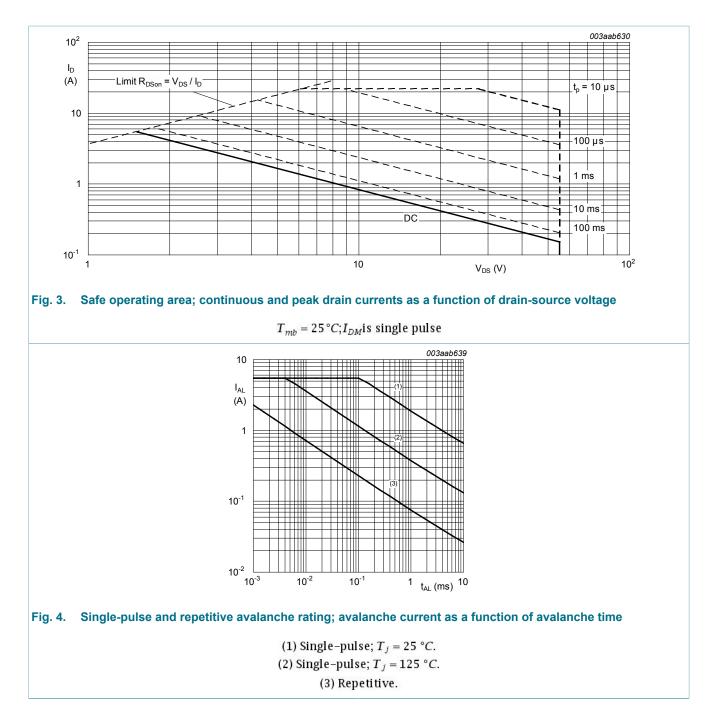
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### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	Fig. 5	-	-	15	K/W

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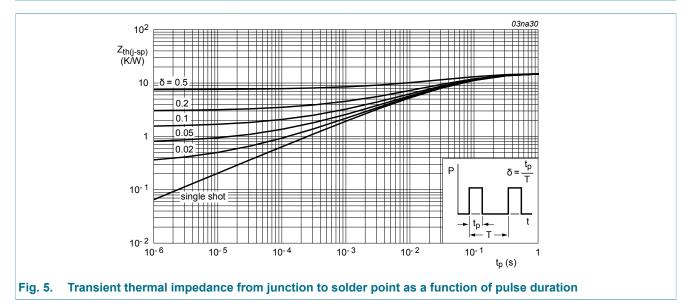
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		-	120	-	K/W



### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics	· · · · ·				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	50	-	-	V
	breakdown voltage	I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	55	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 11	1	1.5	2	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 150 °C; Fig. 11	0.6	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 11	-	-	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 55 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.05	10	μA
		$V_{DS}$ = 55 V; $V_{GS}$ = 0 V; $T_j$ = 150 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 15 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -15 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 150 °C; Fig. 12; Fig. 13	-	-	276	mΩ
		$V_{GS}$ = 4.5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-	-	161	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-	116	137	mΩ

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 12;</u> <u>Fig. 13</u>		-	128	150	mΩ
Dynamic cl	haracteristics						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 44 V; V <sub>GS</sub> = 5 V;		-	5.3	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>		-	1	-	nC
Q <sub>GD</sub>	gate-drain charge	-		-	2.8	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	240	320	pF
C <sub>oss</sub>	output capacitance			-	53	64	pF
C <sub>rss</sub>	reverse transfer capacitance	-		-	40	55	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; $R_L$ = 3.3 $\Omega$ ; $V_{GS}$ = 5 V;		-	8	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C		-	57	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	16	-	ns
t <sub>f</sub>	fall time			-	13	-	ns
Source-dra	iin diode	-					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>		-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 5 A; dI <sub>S</sub> /dt = -100 A/µs;		-	24	-	ns
Qr	recovered charge	V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C		-	30	-	nC

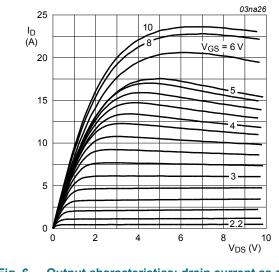


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

 $T_j = 25^{\circ}C; t_p = 300 \mu s$ 

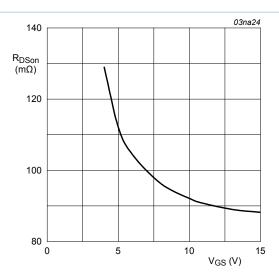


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

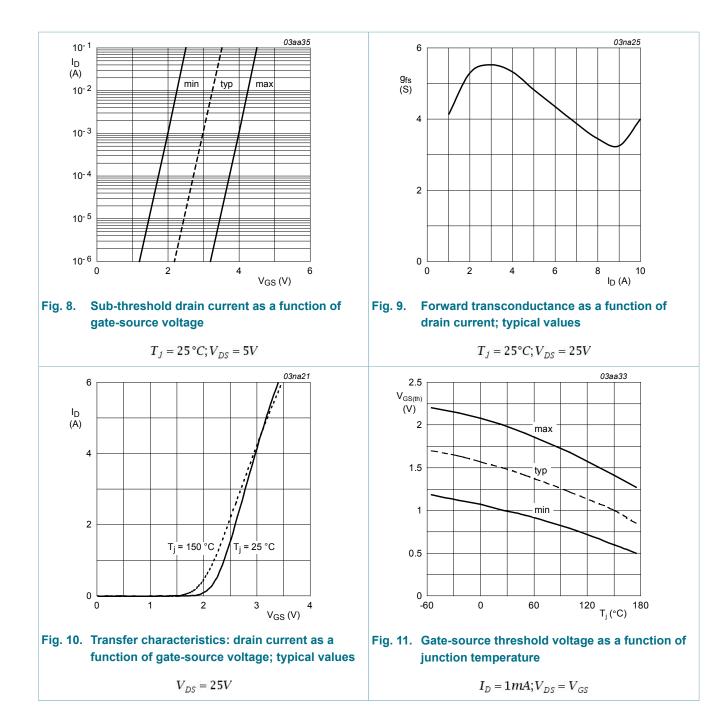
 $T_j = 25^{\circ}C; I_D = 5A$ 

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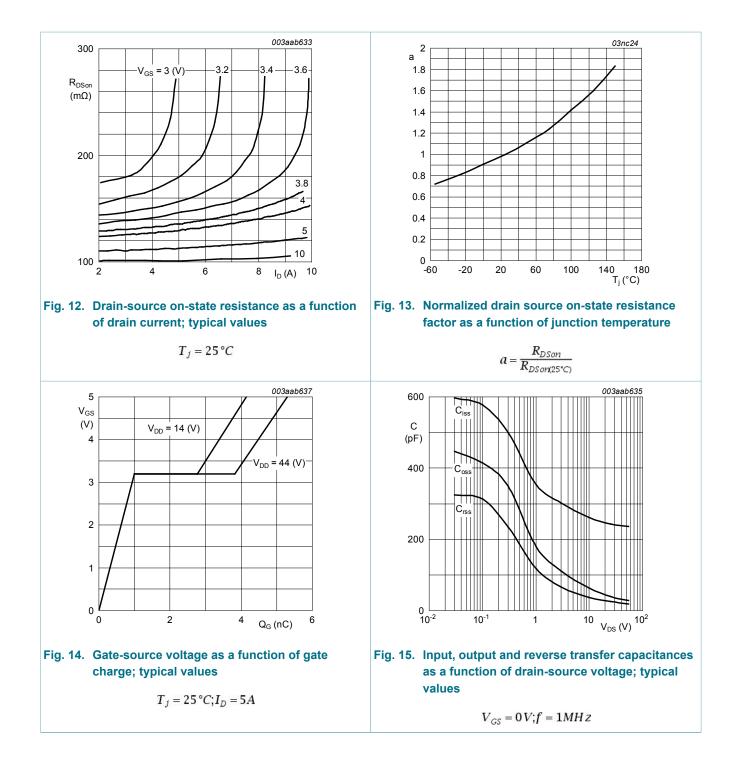
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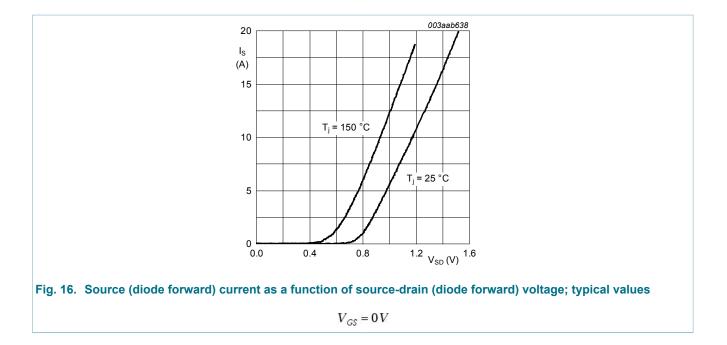
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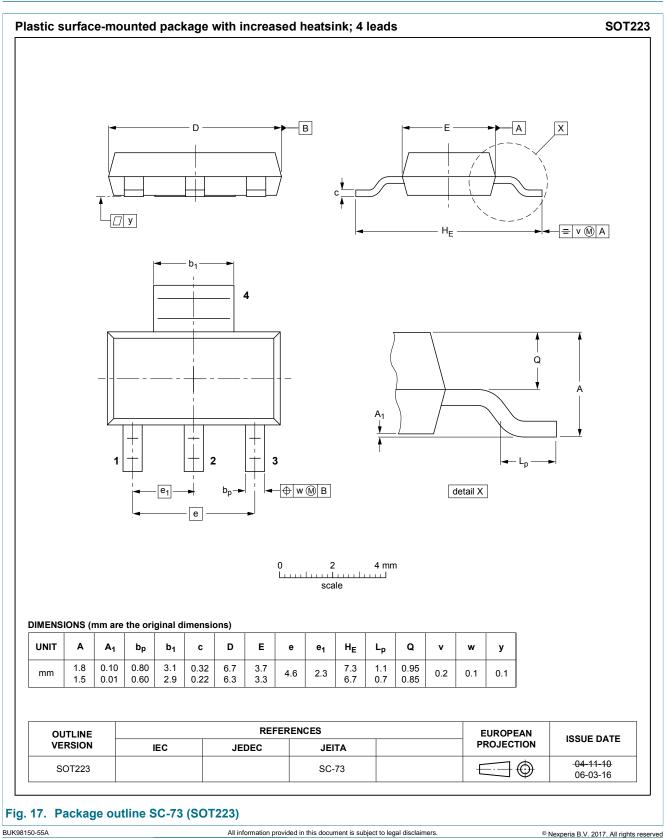


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### 11. Package outline



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### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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